Ordering number:ENN4540

N-Channel Enhancement Silicon MOSFET

3SK248

Muting/Switching Applications

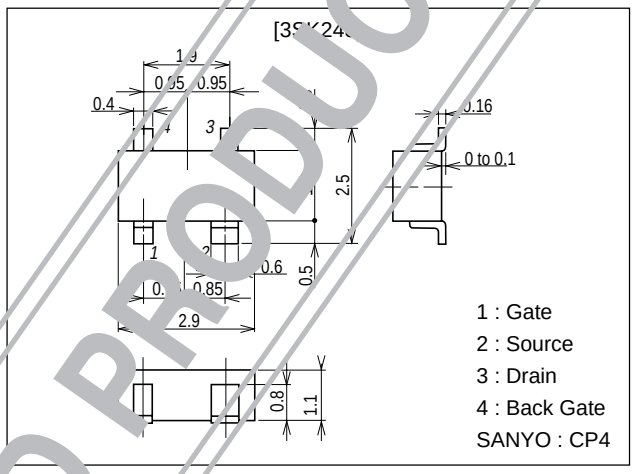
Features

- MOSFET with a back gate terminal.
- Enhancement type.
- Small ON resistance.
- Small-sized package permitting 3SK248-applied sets to be made smaller and slimmer.

Package Dimensions

unit:mm

2100A



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		10	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		100	mA
Allowable Power Dissipation	P_D		200	mW
Channel Temperature	Tch		125	˚C
Storage Temperature	Tstg		–55 to +125	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=10µA, V_{GS}=0V	10			V
Gate-to-Source Breakdown Voltage	V_{GSS}	I_G=±10µA, V_{DS}=0V	±10			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=5V, V_{GS}=0V			1	µA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V		±0.01	±50	nA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=5V, I_D=100µA	0.3		1.5	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=5V, I_D=50mA, f=1kHz		80		mS
Input Capacitance	Ciss	V_{DS}=5V, V_{GS}=0V, f=1MHz		50		pF
Output Capacitance	Coss	V_{DS}=5V, V_{GS}=0V, f=1MHz		10		pF
Reverse Transfer Capacitance	Crss	V_{DS}=5V, V_{GS}=0V, f=1MHz		5		pF

Marking : N

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}1$	V_{GS}=5V, I_D=50mA		5	7	Ω
	$R_{DS(on)}2$	V_{GS}=2.5V, I_D=15mA		7	12	Ω

Electrical Connection